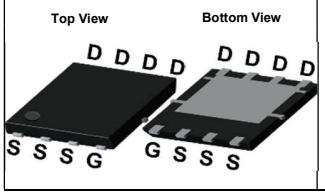
SL68N08G

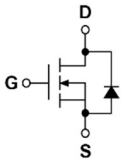
N-Channel Enhancement Mode MOSFET

Pin Description

PDFN3.3*3.3



Symbol



Product Summary

Symbol	N-Channel	Unit
V_{DSS}	80	V
$R_{DS(ON)}$-Max	7.7	mΩ
ID	68	A

Feature

- Advanced trench cell design
- Reliable and Rugged
- ROHS Compliant & Halogen-Free
- 100% UIS and Rg Tested

Applications

- Motor drivers
- DC-DC Converter

Ordering Information

Orderable Part Number	Package Type	Form	Shipping	Marking
SL68N08G	PDFN3.3*3.3	Tape & Reel	5000 / Tape & Reel	

Absolute Maximum Ratings (T_J=25°C Unless Otherwise Noted)

Symbol	Parameter		N-Channel	Unit
V_{DSS}	Drain-Source Voltage		80	V
V_{GSS}	Gate-Source Voltage		±20	
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-55 to 150	°C
I_{DM}①	Pulse Drain Current Tested	T_C=25°C	171	A
I_D	Continuous Drain Current	T_C=25°C	68	A
		T_C=100°C	43	
P_D	Maximum Power Dissipation	T_C=25°C	35.7	W
		T_C=100°C	14.3	
I_D	Continuous Drain Current	T_A=25°C	14.7	A
		T_A=70°C	11.8	
P_D	Maximum Power Dissipation	T_A=25°C	1.7	W
		T_A=70°C	1.1	
I_{AS}②	Avalanche Current, Single pulse	L=0.1mH	25	A
		L=0.5mH	15	
E_{AS}②	Avalanche Energy, Single pulse	L=0.1mH	31	mJ
		L=0.5mH	56	

Thermal Characteristics

Symbol	Parameter		Rating	Unit
$R_{\theta JC}$	Thermal Resistance-Junction to Case	Steady State	3.5	°C/W
$R_{\theta JA}$③	Thermal Resistance-Junction to Ambient	Steady State	75	°C/W

Note ① : Max. current is limited by junction temperature

Note ② : UIS tested and pulse width are limited by maximum junction temperature 150°C

Note ③ : Surface Mounted on 1in^2 FR-4 board with 1oz.

N-Channel Electrical Characteristics (T_J=25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Electrical Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_{DS}=250uA	80	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=64V, V_{GS}=0V	-	-	1	uA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_{DS}=250uA	1	2	3	V
I_{GSS}	Gate Leakage Current	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
$R_{DS(ON)}$●	Drain-Source On-state Resistance	V_{GS}=10V, I_{DS}=20A	-	6.4	7.7	mΩ
		V_{GS}=4.5V, I_{DS}=10A	-	10	13	
gfs	Forward Transconductance	V_{DS}=5V, I_{DS}=10A	-	27	-	S
Dynamic Characteristics ●						
R_G	Gate Resistance	V_{GS}=0V,V_{DS}=0V, Freq.=1MHz	-	1.2	-	Ω
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=40V, Freq.=1MHz	-	1692	-	pF
C_{oss}	Output Capacitance		-	479	-	
C_{rss}	Reverse Transfer Capacitance		-	42	-	
$td_{(ON)}$	Turn-on Delay Time	V_{GS}=10V,V_{DS}=40V, I_D=1A,R_{GEN}=6Ω	-	8	-	nS
t_r	Turn-on Rise Time		-	15.5	-	
$t_{d(OFF)}$	Turn-off Delay Time		-	28.3	-	
t_f	Turn-off Fall Time		-	62	-	
Q_g	Total Gate Charge	V_{GS}=4.5V,V_{DS}=40V I_D=20A	-	20	-	nC
Q_g	Total Gate Charge	V_{GS}=10V,V_{DS}=50V, I_D=20A	-	35	-	
Q_{gs}	Gate-Source Charge		-	8	-	
Q_{gd}	Gate-Drain Charge		-	9.3	-	
Source-Drain Characteristics						
V_{SD}●	Diode Forward Voltage	I_{SD}=10A, V_{GS}=0V	-	0.8	1.1	V
t_{rr}	Reverse Recovery Time	I_F=10A, V_R=40V dI$_F$/dt=100A/μs	-	33	-	nS
Q_{rr}	Reverse Recovery Charge		-	30	-	nC

Note ④：Pulse test (pulse width≤300us, duty cycle≤2%).
Note ⑤：Guaranteed by design, not subject to production testing.

N-Channel Typical Characteristics

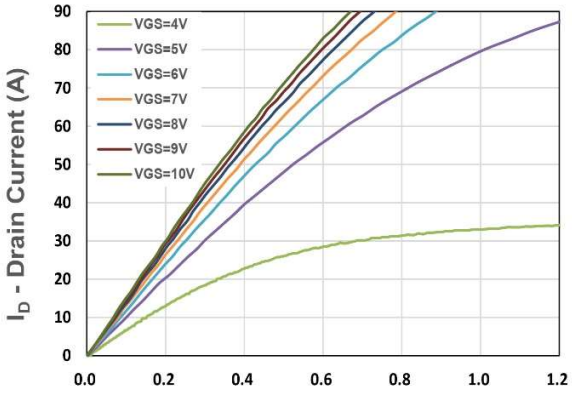


Figure 1. Output Characteristics

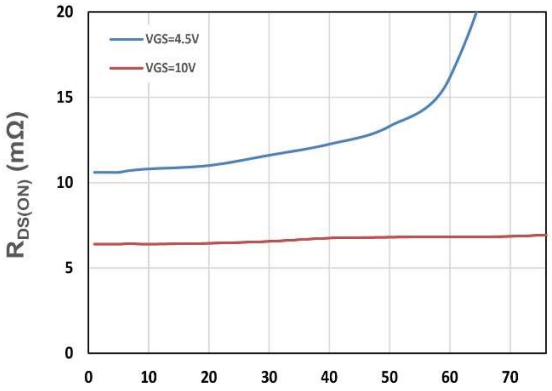


Figure 2. On-Resistance vs. ID

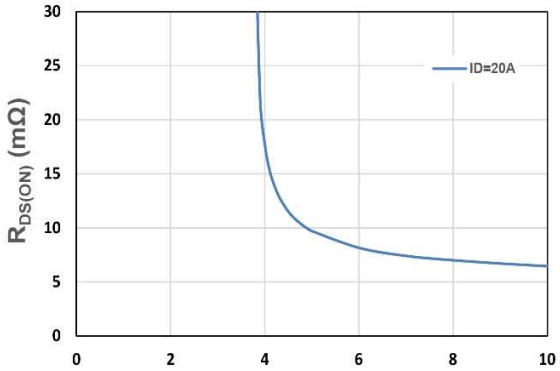


Figure 3. On-Resistance vs. VGS

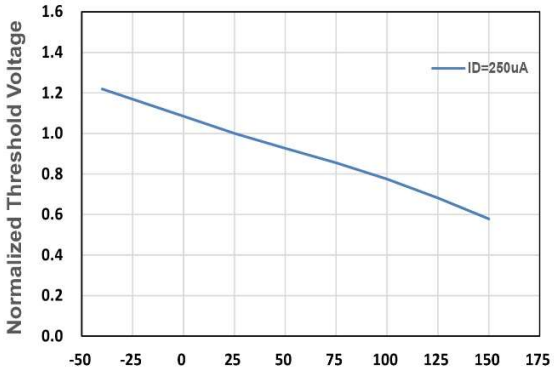


Figure 4. Gate Threshold Voltage

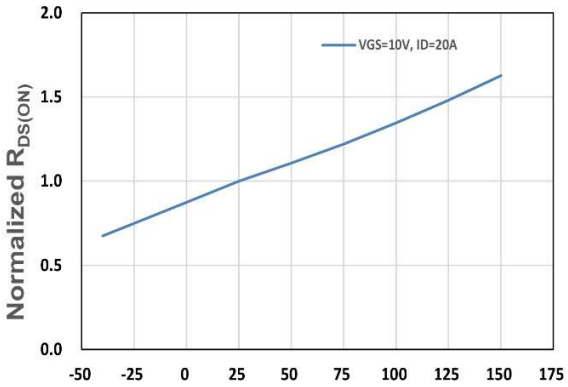


Figure 5. Drain-Source On Resistance

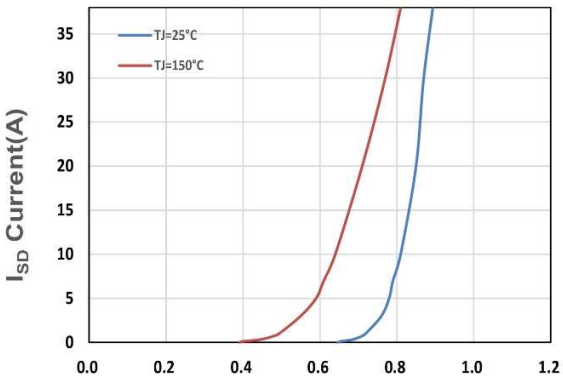


Figure 6. Source-Drain Diode Forward

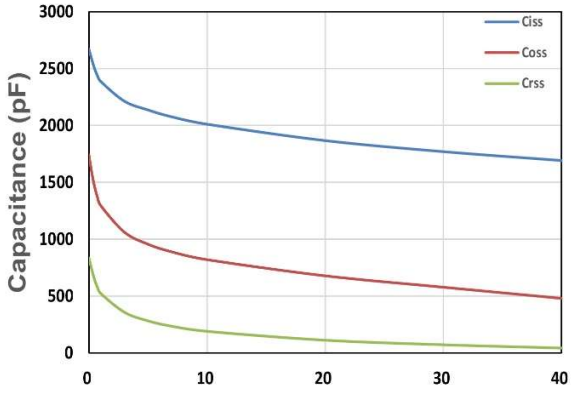


Figure 7. Capacitance

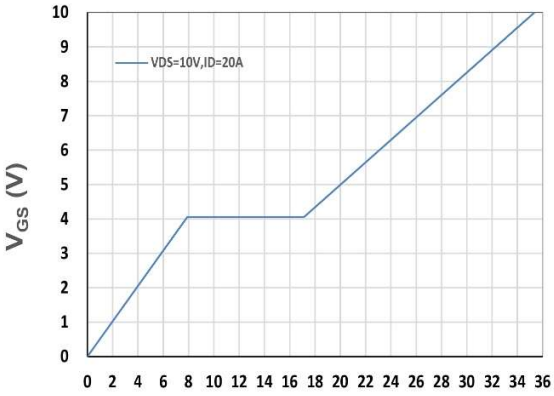


Figure 8. Gate Charge Characteristics

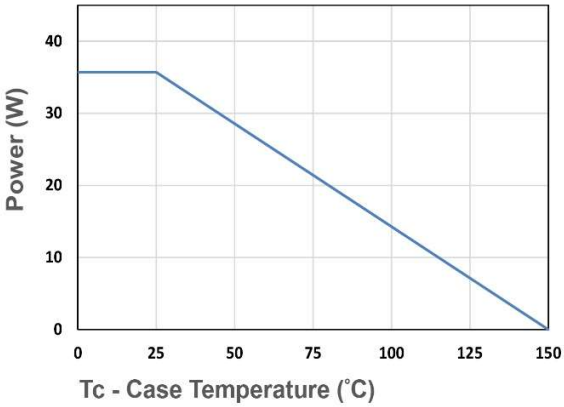


Figure 9. Power Dissipation

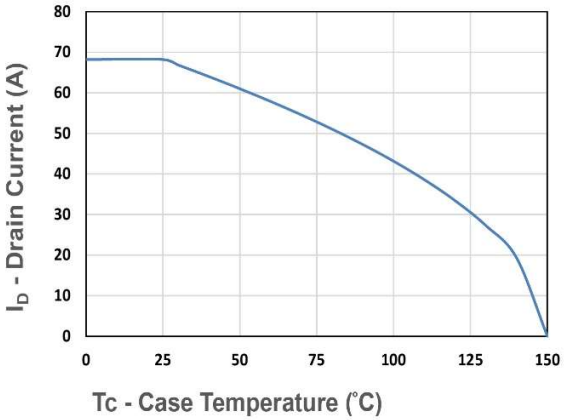


Figure 10. Drain Current

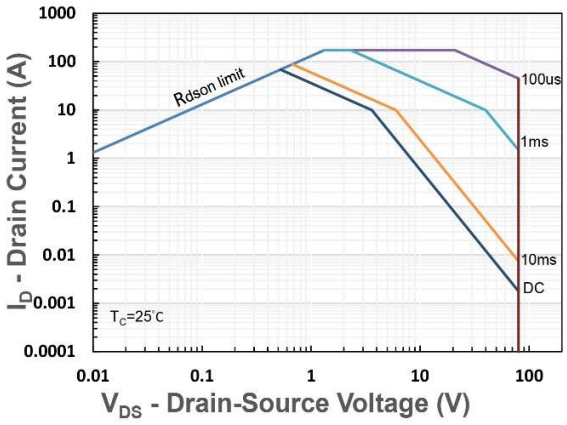


Figure 11. Safe Operating Area

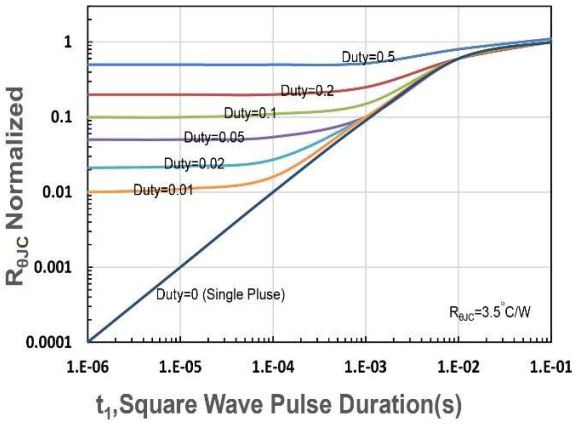


Figure 12. RθJC Transient Thermal Impedance